UNISONIC TECHNOLOGIES CO., LTD

UCBD20120 sic-sbd diode

SILICON CARBIDE SCHOTTKY BARRIER DIODES

■ DESCRIPTION

The **UCBD20120** is an SiC Schottky barrier diodes (SBDs) feature high reverse voltage ratings. In addition to SBDs with short reverse recovery time (trr), provides 1200V SBDs with a junction barrier Schottky (JBS) structure that provide low leakage current (Ir) and high surge current capability required for switched-mode power supplies. These devices help improve the efficiency of switched-mode power supplies.

■ FEATURES

- * Zero Forward/Reverse Recovery Current
- * High Blocking Voltage
- * High Frequency Operation
- * Positive Temperature Coefficient on V_F
- * Temperature Independent Switching Behavior
- * High surge current capability

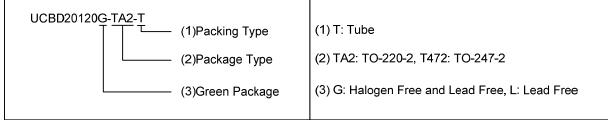




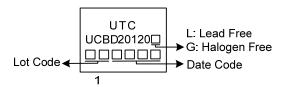
■ ORDERING INFORMATION

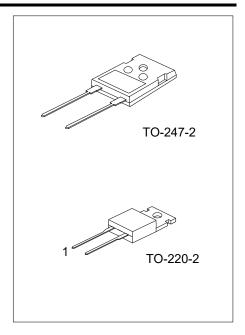
Ordering Number		Daakana	Pin Assignment		Dealine	
Lead Free	Halogen Free	Package	1	2	Packing	
UCBD20120L-TA2-T	UCBD20120G-TA2-T	TO-220-2	K	Α	Tube	
UCBD20120L-T472-T	UCBD20120G-T472-T	TO-247-2	K	Α	Tube	

Note: Pin Assignment: K: Cathode A: Anode



■ MARKING





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■ ABSOLUTE MAXIMUM RATINGS (T_C=25°C, unless otherwise specified)

Ratings at 25°C ambient temperature unless otherwise specified. Resistive or inductive load, 60Hz.

PARAMETER		SYMBOL	RATINGS	UNIT
Repetitive Peak Reverse Voltage		V_{RRM}	1200	V
Surge Peak Reverse Voltage		V_{RSM}	1200	V
DC Blocking Voltage		V_R	1200	V
Continuous Forward Current	T _C =150°C	l _F	20	Α
Repetitive Peak Forward Surge Current	T _J =25°C t _P =10ms, Half Sine Wave		110	A
	T _J =110°C t _P =10ms, Half Sine Wave	I _{FRM}	100	A
Non-Repetitive Peak Forward Surge Current	T _J =25°C t _P =10ms, Half Sine Wave		140	А
	T _J =110°C t _P =10ms, Half Sine Wave	IFSM	130	A
Operating Junction Temperature		TJ	-55 ~ +175	°C
Storage Temperature Range		T _{STG}	-55 ~ +175	°C

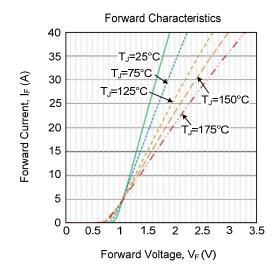
Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

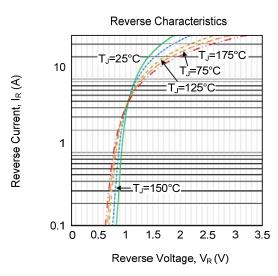
■ ELECTRICAL CHARACTERISTICS

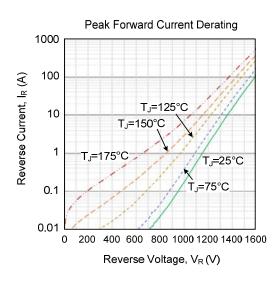
(Ratings at 25°C ambient temperature unless otherwise specified. Resistive or inductive load, 60Hz)

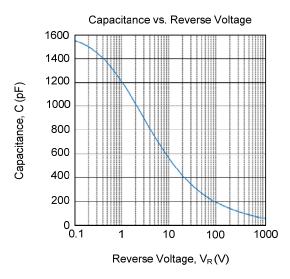
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
DC Blocking Voltage	V _{DC}	T _C =25°C	1200			V
	VF	I _F =20A, T _J =25°C		1.4	1.75	V
Forward Voltage		I _F =20A, T _J =125°C		1.75		V
		I _F =20A, T _J =175°C		1.95		V
		V _R =1200V, T _J =25°C		2	150	μΑ
Reverse Current		V _R =1200V, T _J =125°C		9		μΑ
		V _R =1200V, T _J =175°C		30		μΑ
Total Capacitive Charge	Qc	V _R =800V, T _J =25°C		105		nC
	С	V _R =1.0V, T _J =25°C, f=1MHz		1210		pF
Total Capacitance		V _R =400V, T _J =25°C, f=1MHz		100		pF
		V _R =800V, T _J =25°C, f=1MHz		68		pF

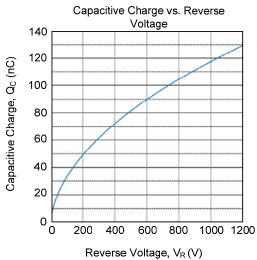
■ TYPICAL CHARACTERISTICS











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